

AMENDMENT TO CLAIMS

1-9. (Canceled)

10. (Previously presented) A method for fabricating a semiconductor device, the method comprising the steps of:

thermally oxidizing a Group III nitride semiconductor layer to form a thermally oxidized insulating film on a surface of the Group III nitride semiconductor layer; and

forming a gate electrode with Schottky characteristic containing an adhesion enhancing element and an element other than the adhesion enhancing element on the thermally oxidized insulating film,

wherein the adhesion enhancing element is Si and a weight percent of the Si in metals composing the gate electrode is not less than 3% and not more than 10%.

11. (Original) The method of claim 10, wherein the step of forming the thermally oxidized insulating film includes the step of:

forming an aluminum nitride layer on the Group III nitride semiconductor layer and then thermally oxidizing the aluminum nitride layer to change the aluminum nitride layer into an aluminum oxide layer and thereby form the thermally oxidized insulating film composed of the aluminum oxide layer.

12. (Original) The method of claim 11, wherein the aluminum oxide layer has a thickness not less than 0.5 nm and not more than 3 nm.

13. (Withdrawn) The method of claim 10, wherein the step of forming the thermally oxidized insulating film includes the step of:

forming a silicon layer on the surface of the Group III nitride semiconductor layer and then thermally oxidizing the silicon layer to change the silicon layer into a silicon oxide layer and thereby form the thermally oxidized insulating film composed of the silicon oxide layer.

14. (Withdrawn) The method of claim 13, wherein the silicon oxide layer has a thickness not less than 0.5 nm and not more than 3 nm.

15-16. (Cancelled)

17. (Previously presented) A method for fabricating a semiconductor device, the method comprising the steps of:

thermally oxidizing a Group III nitride semiconductor layer to form a thermally oxidized insulating film on a surface of the Group III nitride semiconductor layer; and

forming a gate electrode with Schottky characteristic containing an adhesion enhancing element and an element other than the adhesion enhancing element on the thermally oxidized insulating film,

wherein the adhesion enhancing element is Si and a weight percent of the Si in metals composing the gate electrode is not less than 4% and not more than 7%.

18. (Previously presented) The method of claim 17, wherein the step of forming the thermally oxidized insulating film includes the step of:

forming an aluminum nitride layer on the Group III nitride semiconductor layer and then thermally oxidizing the aluminum nitride layer to change the aluminum nitride layer into an aluminum oxide layer and thereby form the thermally oxidized insulating film composed of the aluminum oxide layer.

19. (Previously presented) The method of claim 18, wherein the aluminum oxide layer has a thickness not less than 0.5 nm and not more than 3 nm.

20. (Cancelled)